

ABSTRACT

1 A device for prolonging lifetime of nonvolatile memory applied to
2 connect a host electronic machine with a nonvolatile memory device comprises a
3 RAM (Random Access Memory) buffer zone, a counter, and two sets of inverters,
4 wherein the RAM buffer zone is employed to store a unit data train temporarily;
5 the counter will count the total bits of logic "0"; and the interpolated inverters are
6 elaborated to lessen the times for reading/writing a nonvolatile memory device by
7 checking a state flag to decide whether a logic inversion of the unit data train is
8 needed or not so as to write lesser bits of logic "0" and thereby prolong the lifetime
9 of the nonvolatile memory.